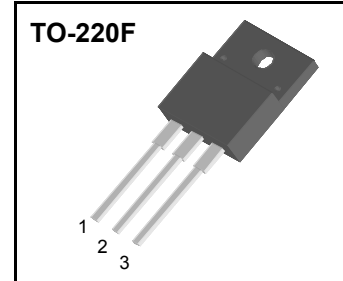


$V_{DRM} = 600V$   
 $I_{T(RMS)} = 8 A$   
 $I_{TSM} = 84A$



### Features

- ◆ Repetitive Peak Off-State Voltage : 600V
- ◆ R.M.S On-State Current (  $I_{T(RMS)} = 8 A$  )
- ◆ High Commutation  $dv/dt$

### General Description

This device is fully isolated package suitable for AC switching application, phase control application such as fan speed and temperature modulation control, lighting control and static switching relay.

This device may substitute for BTA08-600, BTB08-600, BT137-600, BCR8PM-12, TM861M/S series.

### Absolute Maximum Ratings ( $T_j = 25^\circ C$ unless otherwise specified )

Symbol	Parameter	Condition	Ratings	Units
$V_{DRM}$	Repetitive Peak Off-State Voltage	Since wave, 50 to 60Hz	600	V
$I_{T(RMS)}$	R.M.S On-State Current	$T_j = 125^\circ C$ , Full Sine wave	8.0	A
$I_{TSM}$	Surge On-State Current	One Cycle, 50Hz/60Hz, Peak, Non-Repetitive	80/84	A
$I^2t$	$I^2t$	$t_p=10ms$	32	$A^2s$
$P_{G(AV)}$	Average Gate Power Dissipation	$T_j=125^\circ C$	1	W
$I_{GM}$	Peak Gate Current	$T_j=125^\circ C$	2	A
$T_J$	Operating Junction Temperature		- 40 ~ 125	$^\circ C$
$T_{STG}$	Storage Temperature		- 40 ~ 150	$^\circ C$



# TF8A60

## Electrical Characteristics (T<sub>j</sub>=25 °C unless otherwise specified)

Symbol	Items		Conditions	Ratings			Unit
				Min.	Typ.	Max.	
I <sub>DRM</sub>	Repetitive Peak Off-State Current		V <sub>D</sub> = V <sub>DRM</sub> , Single Phase, Half Wave T <sub>j</sub> = 125 °C	—	—	2	mA
V <sub>TM</sub>	Peak On-State Voltage		I <sub>TM</sub> = 11 A, T <sub>P</sub> =380μs	---	—	1.55	V
I <sup>+</sup> <sub>GT1</sub>	I	Gate Trigger Current	V <sub>D</sub> = 12 V, R <sub>L</sub> =30 Ω	—	—	30	mA
I <sup>-</sup> <sub>GT1</sub>	II			—	—	30	
I <sup>-</sup> <sub>GT3</sub>	III			—	—	30	
V <sup>+</sup> <sub>GT1</sub>	I	Gate Trigger Voltage	V <sub>D</sub> = 12 V, R <sub>L</sub> =30 Ω	—	—	1.5	V
V <sub>GT1</sub>	II			—	—	1.5	
V <sub>GT3</sub>	III			—	—	1.5	
V <sub>GD</sub>	Non-Trigger Gate Voltage		T <sub>j</sub> = 125 °C, V <sub>D</sub> = V <sub>DRM</sub> , R <sub>L</sub> =3.3K Ω	0.2	---	—	V
dv/dt	Critical Rate of Rise Off-State Voltage		T <sub>j</sub> = 125 °C, V <sub>D</sub> =2/3 V <sub>DRM</sub>	200	---	---	V/μs
I <sub>H</sub>	Holding Current		I <sub>T</sub> =0.2A	--	--	50	mA



# TF8A60

Fig 1. Gate Characteristics

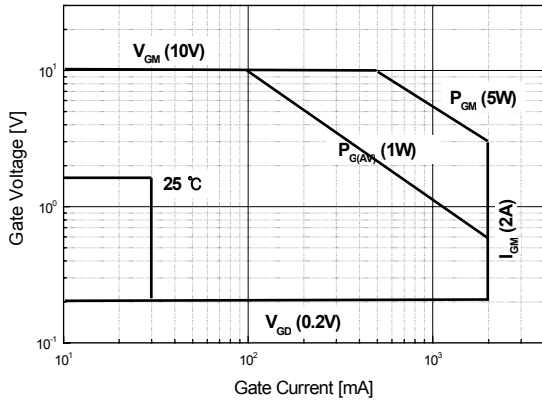


Fig 2. On-State Voltage

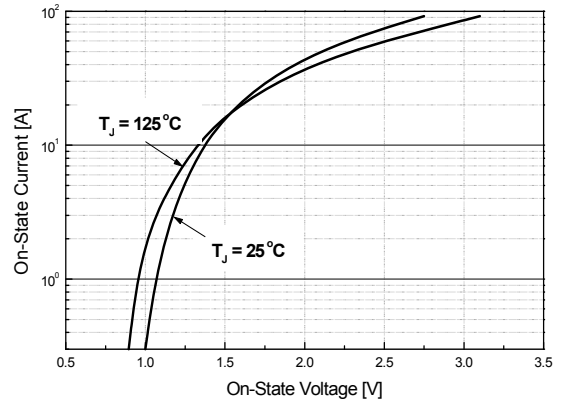


Fig 3. On State Current vs. Maximum Power Dissipation

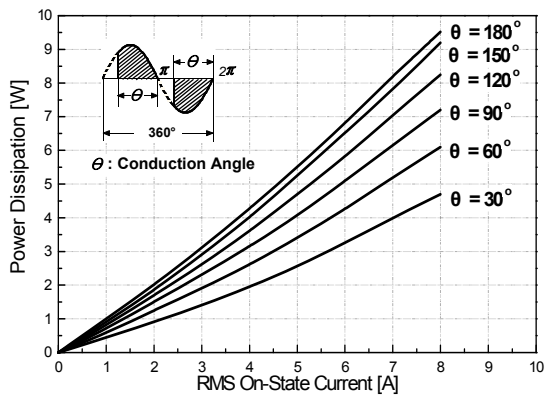


Fig 4. On State Current vs. Allowable Case Temperature

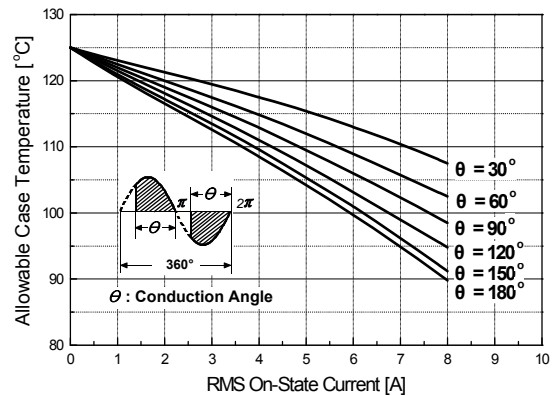


Fig 5. Surge On-State Current Rating ( Non-Repetitive )

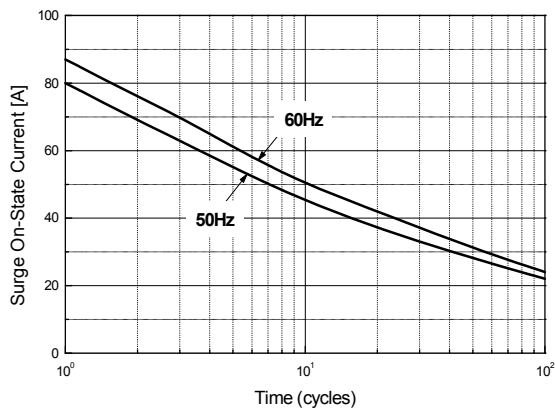


Fig 6. Gate Trigger Voltage vs. Junction Temperature

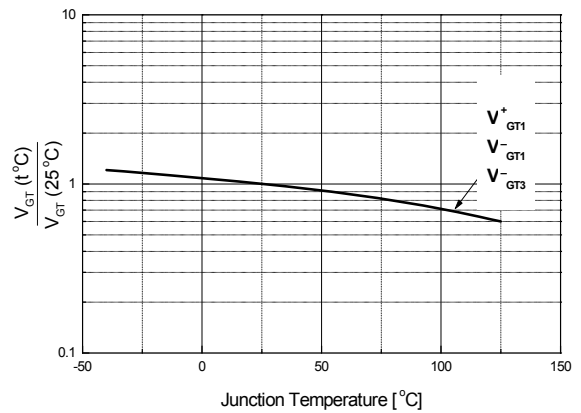




Fig 7. Gate Trigger Current vs. Junction Temperature

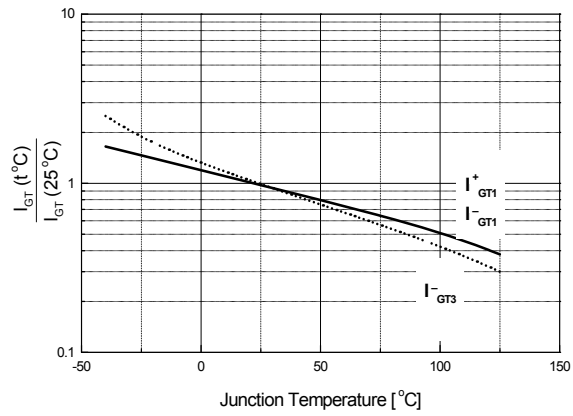
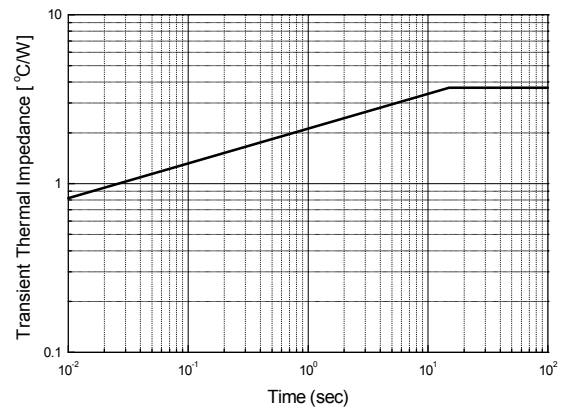


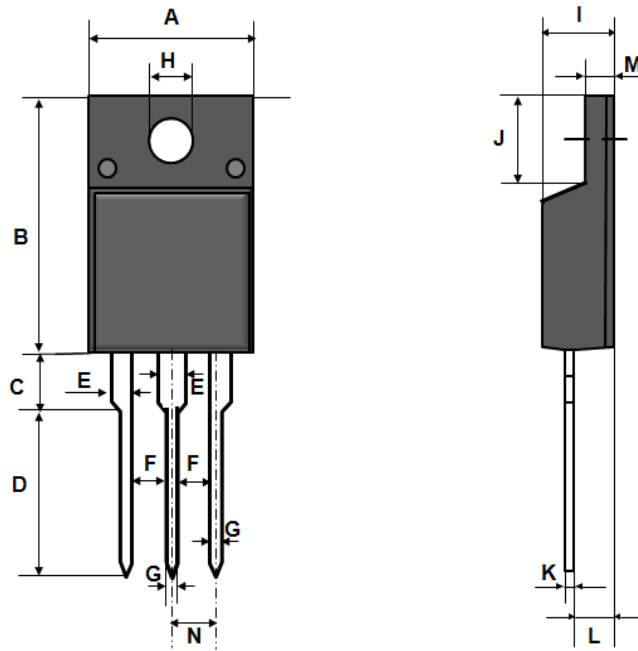
Fig 8. Transient Thermal Impedance





# TF8A60

## TO-220F Package Dimension



Symbol	INCHES			MILLIMETERS		
	MIN	TYP	MAX		MIN	TYP
A	9.88	10.08	10.28	25.10	25.60	26.11
B	15.30	15.50	15.70	38.86	39.37	39.88
C	2.95	3.00	3.05	7.49	7.62	7.75
D	10.30	10.50	10.70	26.16	26.67	27.18
E	0.95	1.08	1.20	2.41	2.74	3.05
F	1.81	1.84	1.87	4.60	4.67	4.75
G	0.50	0.70	0.90	1.27	1.78	2.29
H	3.00	3.20	3.40	7.62	8.13	8.64
I	4.35	4.45	4.55	11.05	11.30	11.56
J	6.20	6.40	6.60	15.75	16.26	16.76
K	0.41	0.51	0.61	1.03	1.28	1.54
L	2.30	2.50	2.70	5.84	6.35	6.86
M	2.53	2.73	2.93	6.43	6.93	7.44
N	2.34	2.54	2.74	5.94	6.45	6.96



## TO-220F Package Dimension, Forming

Dim.	mm			Inch		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	10.4		10.6	0.409		0.417
B	6.18		6.44	0.243		0.254
C	9.55		9.81	0.376		0.386
D	8.4		8.66	0.331		0.341
E	6.05		6.15	0.238		0.242
F	1.26		1.36	0.050		0.054
G	3.17		3.43	0.125		0.135
H	1.87		2.13	0.074		0.084
I	2.57		2.83	0.101		0.111
J		2.54			0.100	
K		5.08			0.200	
L	2.51		2.62	0.099		0.103
M	1.23		1.36	0.048		0.054
N	0.45		0.63	0.018		0.025
O	0.65		0.78	0.0025		0.031
P		5.0			0.197	
$\phi$		3.7			0.146	
$\phi 1$		3.2			0.126	
$\phi 2$		1.5			0.059	

